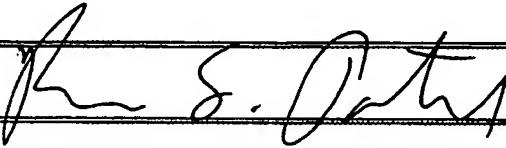


FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 05-720-US2	Serial No. 10/559,981
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use several sheets if necessary)			
<b>Applicant:</b> Kouvettakis, et al.			
<b>Filing Date:</b> December 8, 2005 <b>Group:</b> 2812			

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EXAMINER	DATE CONSIDERED
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